MOSFETs Silicon N-channel MOS (U-MOSIV)

TPCP8011

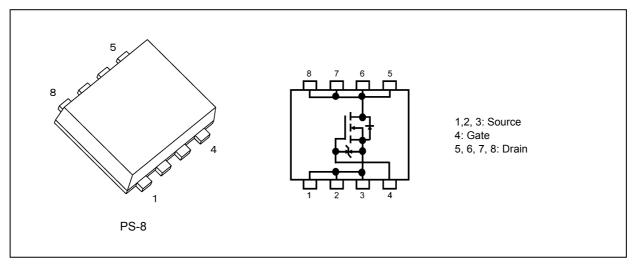
1. Applications

- Motor Drivers
- Mobile Equipment

2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Small gate charge : $Q_{SW} = 4.7 \text{ nC}$ (typ.)
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 25.5 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (5) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 40 \ V)$
- (6) Enhancement mode: $V_{th} = 2$ to 3 V ($V_{DS} = 10$ V, $I_D = 1$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V _{DSS}	40	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)		(Note 1)	Ι _D	5	Α
Drain current (pulsed)		(Note 1)	I _{DP}	20	
Power dissipation	(t = 5 s)	(Note 2)	PD	1.96	W
Power dissipation	(t = 5 s)	(Note 3)	PD	0.94	W
Single-pulse avalanche energy		(Note 4)	E _{AS}	33.2	mJ
Avalanche current			I _{AR}	5	Α
Channel temperature		(Note 5)	T _{ch}	175	°C
Storage temperature		(Note 5)	T _{stg}	-55 to 175	7

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics				Max	Unit
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 2)	R _{th(ch-a)}	76.5	°C/W
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 3)	R _{th(ch-a)}	159.5	°C/W

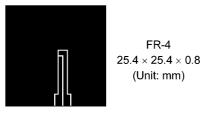
Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 1.379 mH, R_G = 1 Ω , I_{AR} = 5 A

Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.



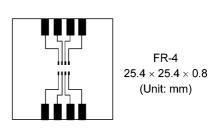
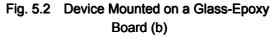


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

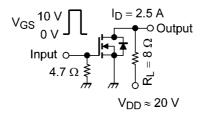
6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	_	_	±10	μA
Drain cut-off current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	40	_	_	V
Drain-source breakdown voltage	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	20	—	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2	2.5	3	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 6 V, I _D = 2.5 A	_	32	51.2	mΩ
		V _{GS} = 10 V, I _D = 2.5 A		25.5	31.8	

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		505	_	pF
Reverse transfer capacitance	C _{rss}			66	_	
Output capacitance	C _{oss}			115	_	
Switching time (rise time)	tr	See Figure 6.2.1	_	5.37	_	ns
Switching time (turn-on time)	t _{on}]		12	_	
Switching time (fall time)	t _f]		4.34	_	
Switching time (turn-off time)	t _{off}]	_	17.4	_	



Duty \leq 1%, t_w = 10 μ s

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

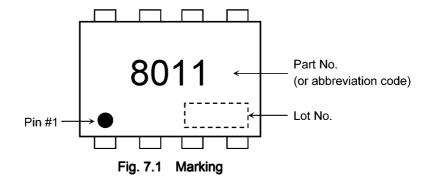
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 32 \text{ V}, \text{ V}_{GS} \text{ = } 10 \text{ V}, \text{ I}_{D} \text{ = } 5 \text{ A}$	—	11.8	—	nC
Gate-source charge 1	Q _{gs1}			2.1	_	
Gate-drain charge	Q _{gd}		_	3.9	_	
Gate switch charge	Q _{SW}		_	4.7	_	

6.4. Source-Drain Characteristics (Ta = 25°C unless otherwise specified)

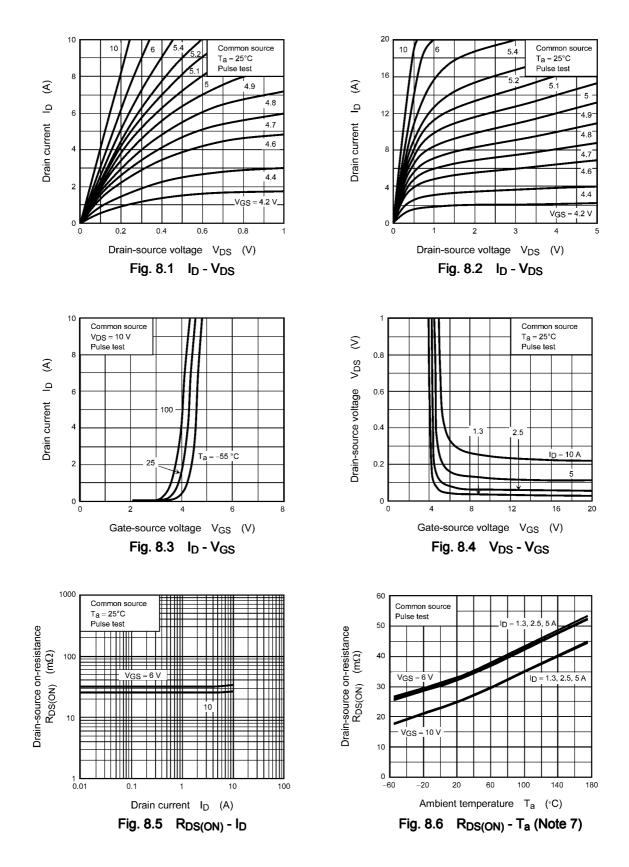
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 6)	I _{DRP}	—	_	—	20	А
Diode forward voltage	V _{DSF}	I _{DR} = 5 A, V _{GS} = 0 V			-1.2	V

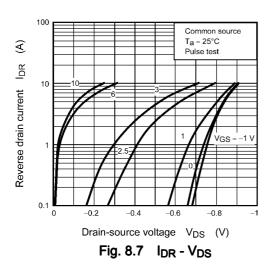
Note 6: Ensure that the channel temperature does not exceed 175°C.

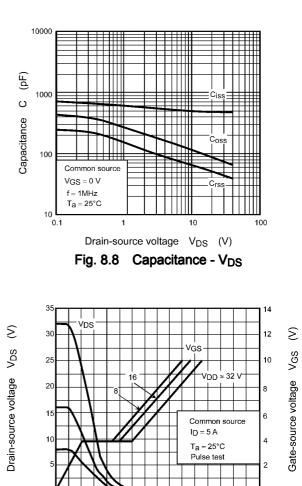
7. Marking

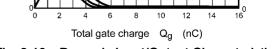


8. Characteristics Curves (Note)





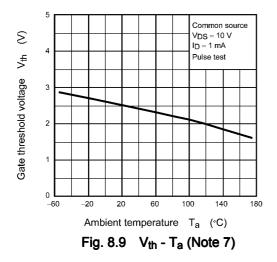


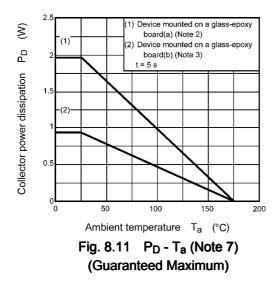


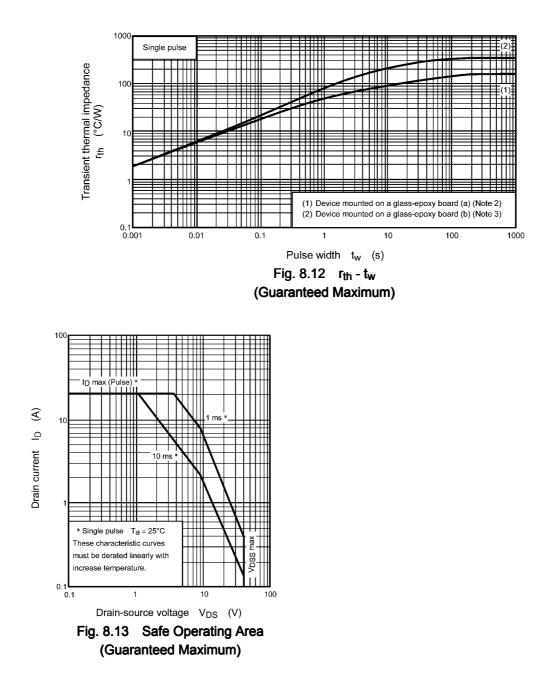
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10 12 14

Fig. 8.10 Dynamic Input/Output Characteristics



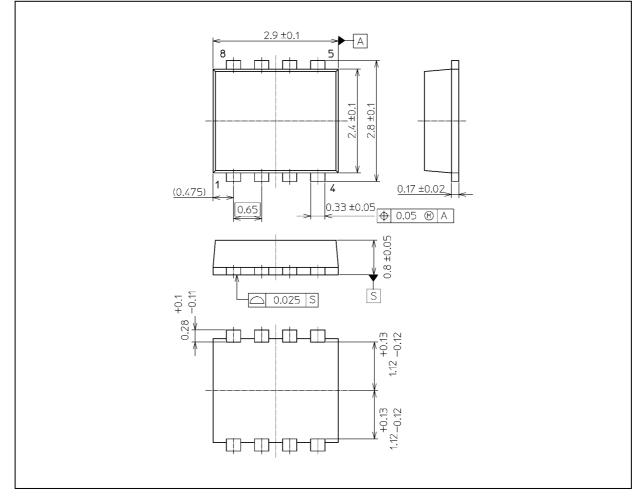




- Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.
- Note 7: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

Package Dimensions

Unit: mm



Weight: 0.017 g (typ.)

Package Name(s)

TOSHIBA: 2-3V1S

Nickname: PS-8

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